

General Description

The AGM016T08LL combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

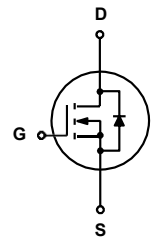
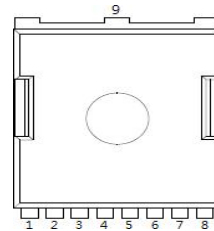
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Package Marking and Ordering Information

Product Summary

BVDSS	RDSON	ID
85V	1.85mΩ	280A

TOLL-8L Pin Configuration



Pin	Description
1	Gate(G)
2,3,4,5,6,7,8	Source(S)
9	Drain(D)

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM016T08LL	AGM016T08LL	TOLL-8L	----	----	2000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	85	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	280	A
	Drain Current-Continuous(Tc=100°C)	231	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	1050	A
PD	Maximum Power Dissipation(Tc=25°C)	378	w
	Maximum Power Dissipation(Tc=100°C)	151	w
EAS	Avalanche energy (Note 3)	2000	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	42	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	0.33	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	85	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=70V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	2.0	--	4.0	V
gFS	Forward Transconductance	VDS=5V,ID=12A	--	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=50A	--	1.85	2.3	mΩ
		VGS=4.5V, ID=25A	--	--	--	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=42V,VGS=0V, F=1MHZ	--	10374	--	pF
Coss	Output Capacitance		--	1736	--	pF
Crss	Reverse Transfer Capacitance		--	16	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=42V, ID=50A,RGEN=4.5Ω	--	28	--	nS
tr	Turn-on Rise Time		--	74	--	nS
td(off)	Turn-Off Delay Time		--	86	--	nS
tf	Turn-Off Fall Time		--	33	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=42V, ID=50A	--	140	--	nC
Qgs	Gate-Source Charge		--	56	--	nC
Qgd	Gate-Drain Charge		--	26	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	280	A
VSD	Forward on Voltage	VGS=0V,IS=50A	--	--	1.2	V
trr	Reverse Recovery Time	IF=50A , dl/dt=100A/μs , TJ=25°C	--	115	--	ns
Qrr	Reverse Recovery Charge		--	320	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

Typical Electrical and Thermal Characteristics

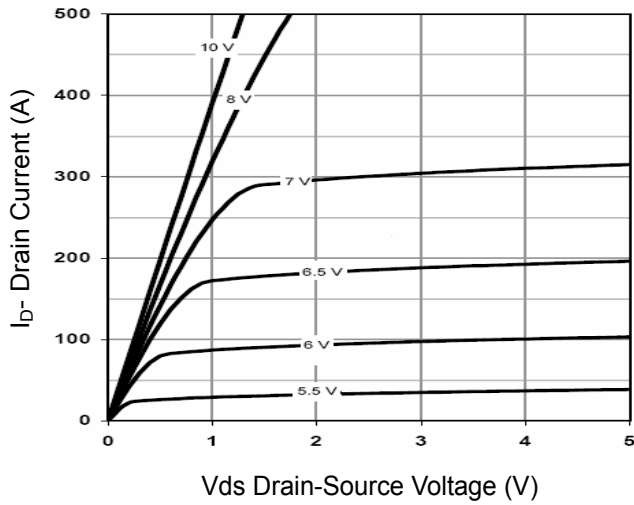


Figure 1 Output Characteristics

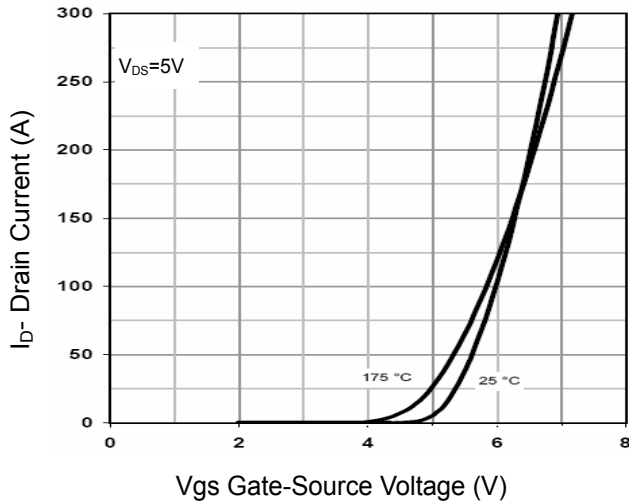


Figure 2 Transfer Characteristics

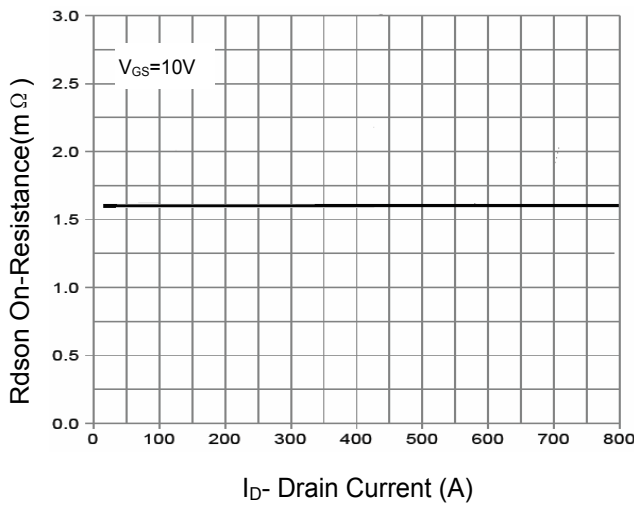


Figure 3 $R_{DS(on)}$ - Drain Current

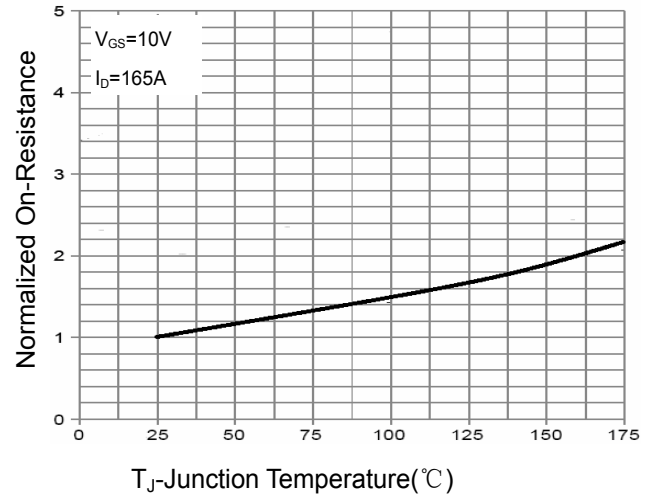


Figure 4 $R_{DS(on)}$ -Junction Temperature

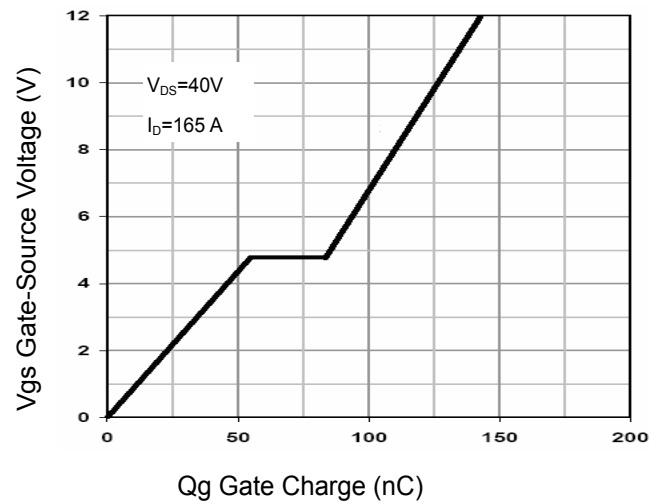


Figure 5 Gate Charge

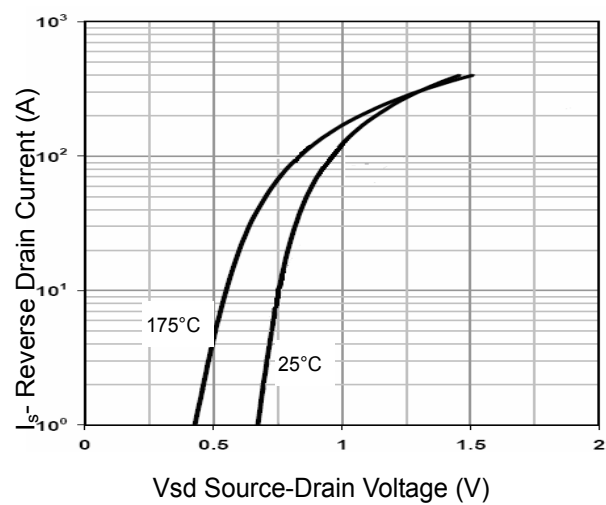


Figure 6 Source- Drain Diode Forward

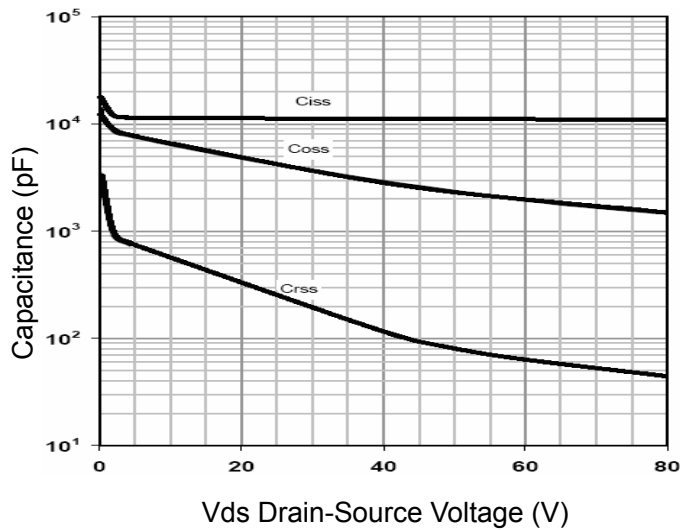


Figure 7 Capacitance vs Vds

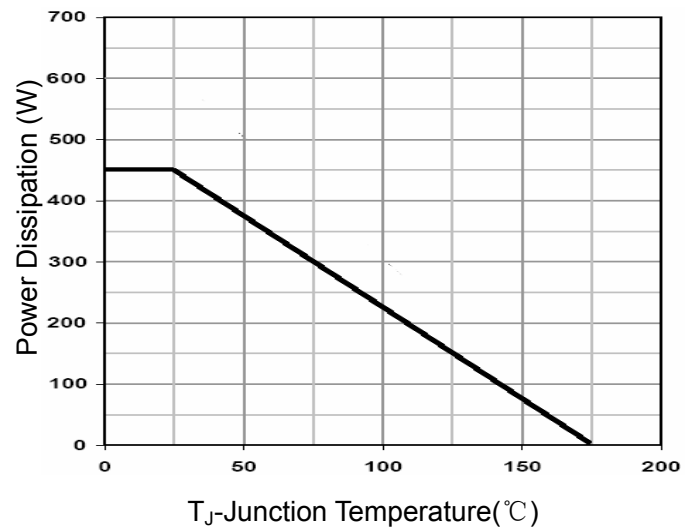


Figure 9 Power De-rating

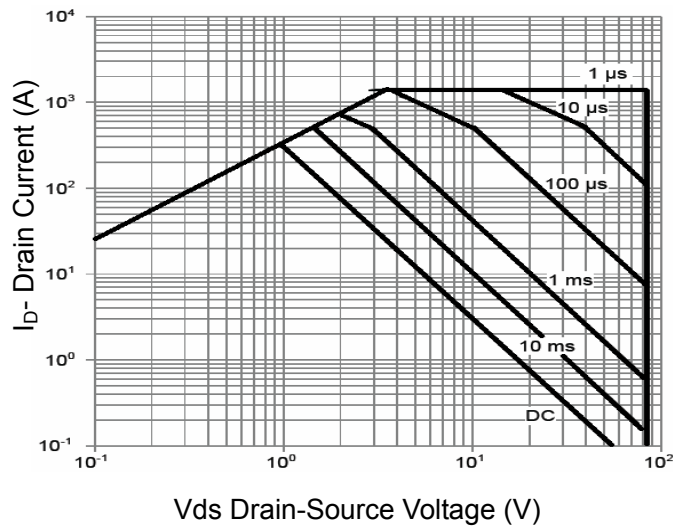


Figure 8 Safe Operation Area

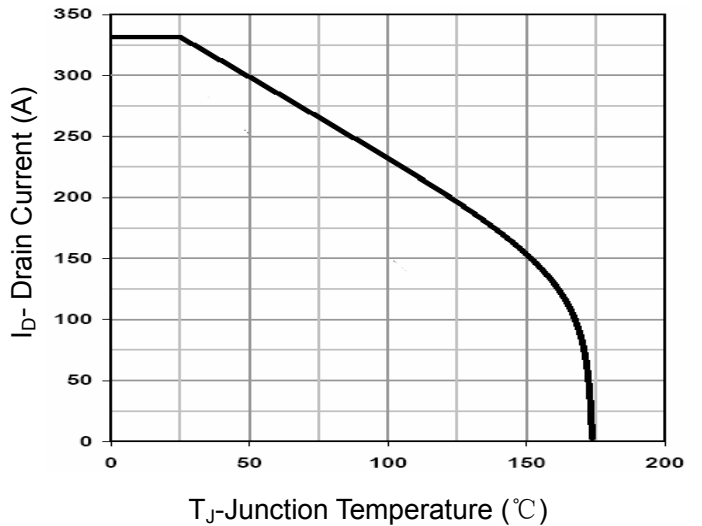


Figure 10 Current De-rating

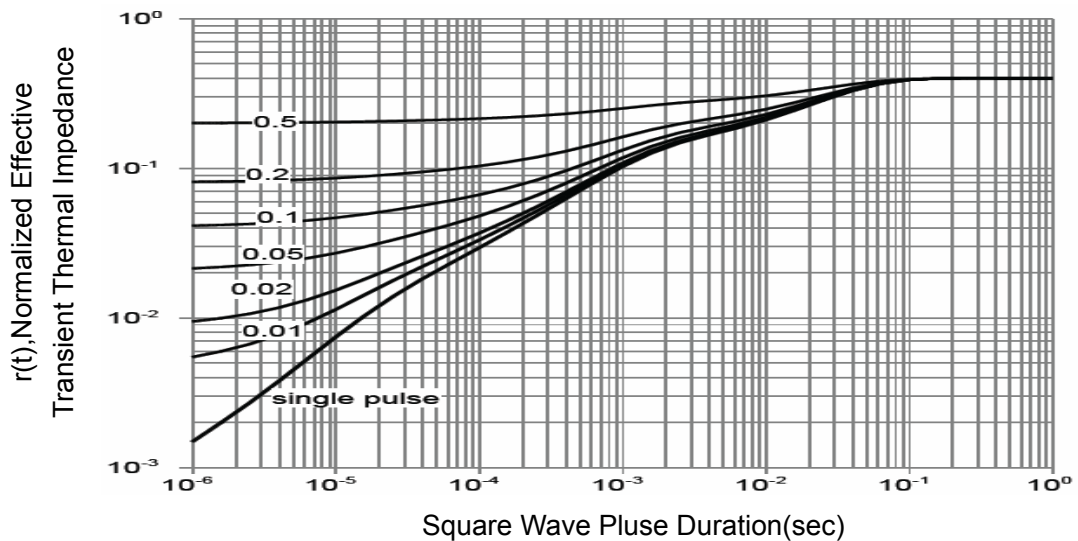


Figure 11 Normalized Maximum Transient Thermal Impedance

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